Preliminary



## SANYO Semiconductors

DATA SHEET

STK760-221A-E — Single-phase Rectification

# **Thick-Film Hybrid IC PFC Hybrid IC**

#### Overview

The STK760-221A-E is an average current control type hybrid IC that integrates in a single package the power stages for the step-up active converter and the control IC, and overcurrent/overvoltage protection circuits. It is designed to improve the power factor of single-phase AC power supplies.

### Applications

• Power rectification for air conditioners and general-purpose inverters as a single-phase rectification active converter.

#### Features

- IGBT switching power device employed in the active converter output stage.
- On-chip regulator for PFC control supports a wide range of input voltage (up to 50V).
- Full complement of protection circuits, including overcurrent, overvoltage, and undervoltage protection, plus soft start function.
- Logic level PFC controlled ON/OFF control.
- On-chip light-load correction circuit that minimizes output voltage increase when no load is applied.
- SIP package providing a high degree freedom for mounting the IC in the set.

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### **Specifications**

Absolute maximum ratings at  $Tc = 25^{\circ}C$ 

Parameter		Symbol	Conditions	Ratings	unit	
IGBT Collector-to-emitter voltage		VCES		600	V	
(TR2+TR3)	Repetitive pe	Repetitive peak collector current		*1	180	А
	Collector curr	Collector current			70	А
	Allowable por	Allowable power dissipation			166	W
FRD	Diode reverse	e voltage	VRM		600	V
(D2)	Repetitive pe	Repetitive peak forward current		*1	160	А
	Forward Curr	Forward Current			41	А
	Allowable por	wer dissipation	Pd		73	W
FRD	Repetitive pe	ak forward current	IFP	*1	15	А
(D3)	Forward curre	Forward current			7	А
	Allowable po	wer dissipation	Pd		13	W
Supply voltage	(Pin 1)		Vs		21 to 50	V
Supply current	(Pin 1)		lsc		60	mA
Signal pin input voltage Pin 5 Pin 12 Pin 13 Pin 9		VVDET				
		VEI		-0.3 to 5.0	V	
		VOVP				
		VIS		-10 to 5.0	V	
		Pin 4	VONF		-0.3 to $V_{CC}$	V
Oscillation freq	uency		fosc		40	kHz
Maximum AC ii	nput voltage		VAC	Single-phase full-wave rectification waveform voltage	264	V
Maximum output voltage		VO	Under the operating conditions of the 44 application circuit		V	
Input current (in steady state)		IIN	Under the operating conditions of the application circuit.		Arms	
Load power			Wo	VAC=200V		kW
Chip junction temperature		Tj		150	°C	
Operating case temperature		Тс	Center of the resin package on the reverse side *2 -20 to +105		°C	
Storage temperature		Tstg		-40 to +125	°C	
Tightening torque			M4 screws *3 1.		N • m	
Dielectric strength voltage			VINS	Sine wave, 50Hz, AC 1 minute *4	2000	VRMS

\*1. Repetitive peak current with the duty ratio of D=0.1 and tp=1ms.

\*2. The measurement point must be within 10 millimeters square wide in the center of the resin package on the reverse side.

\*3. The tightening torque must be within the range of 0.79 to 1.17N • m.

The flatness of the heat sink to be connected must be 0.15mm or less.

\*4. Test conditions: AC 2500V for 1 second.

#### Electrical Characteristics at Tc=25°C, Vs=21V with the designated circuit

Parameter	Symbol	Conditions	min	typ	max	unit	Test circuit
Power output block							
Collector-to-emitter cutoff current (TR2+TR3)	ICES	V <sub>CE</sub> =600V			200	μΑ	Fig.1
Collector-to-emitter saturation voltage (TR2+TR3)	V <sub>CE</sub> (sat)	V <sub>CC</sub> =18.0V, I <sub>C</sub> =40A		1.9	2.4	V	Fig.2
Diode reverse voltage (D2)	IR	V <sub>R</sub> =600V			100	μΑ	Fig.1
Diode forward voltage (D2)	٧ <sub>F</sub>	I <sub>F</sub> =40A		2.1	2.6	V	Fig.3
Diode forward voltage (D3)	٧ <sub>F</sub>	I <sub>F</sub> =5A		2.5	3.5	V	Fig.3
Junction-to-case thermal resistance	θj-с1	IGBT (TR2+TR3)		0.75		°C /W	
	θj-c2	FRD (D2)		1.7		°C /W	
	өј-сЗ	FRD (D3)		9.0		°C /W	

(Apply V<sub>CC</sub>=18.0V directly to pin 2 unless Vs input is specified.)

Continued on next page.

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Parameter	Symbol	Conditions	min	typ	max	unit	Test circuit	
V <sub>CC</sub> regulator block								
$V_{CC}$ regulator output voltage	Vcc	Vs=21V, I <sub>CC</sub> OUT=0 to 40mA	17.9	18.7	19.6	V	Fig.4	
Control IC block								
Control circuit current dissipation	I <sub>CC</sub> (ON)	V <sub>CC</sub> =18.0V, ONF=5V		7	11	mA	_	
	I <sub>CC</sub> (OFF)	V <sub>CC</sub> =18.0V, ONF=0V		0.06	0.5	mA	Fig.5	
Reference voltage	VREF	V <sub>CC</sub> =18.0V, ONF=5V	4.75	5.0	5.25	V	Fig.5	
Oscillation frequency	fosc	V <sub>CC</sub> =18.0V, ONF=5V	19.3	21.5	23.7	kHz		
Overcurrent protection input threshold voltage	VTHOCP	V <sub>CC</sub> =18.0V, ONF=5V	-1.20	-1.10	-1.00	V	Fig.6	
Voltage error amplifier reference voltage	Vr	V <sub>CC</sub> =18.0V, ONF=5V	1.509	1.55	1.591	V	]	
OVP threshold voltage	VTHOVP	V <sub>CC</sub> =18.0V, ONF=5V	1.607	1.64	1.673	V	Fig.7	
SS charge current	ICHG	V <sub>CC</sub> =18.0V, ONF=5V		11		μΑ		
SS input threshold voltage	VTHSSO	Duty cycle=0%		0.34		V		
	VTHSSM	Duty cycle=D <sub>MAX</sub>		3.4		V		
ON/OFF threshold voltage	VTHON	V <sub>CC</sub> =18.0V	3.5	3.95	4.4	V	Fig.8	
	VTHOFF	V <sub>CC</sub> =18.0V	2.4	2.8	3.2	V		
Startup V <sub>CC</sub> voltage	VTHUON	ONF=5V	15.5	16.5	17.5	V	E. O	
Shutdown V <sub>CC</sub> voltage	VTHUOFF	ONF=5V	8.2	8.9	9.6	V	Fig.9	
Power output block								
Switching time	tON	I <sub>C</sub> =30A, Inductive load	0.2	0.35	0.8	μs		
	<sup>t</sup> OFF			0.85	1.4	μs	<b>Fig. 10</b>	
	t <sub>rr</sub>	]		0.04		μs	Fig.10	
Diode recovery current (D2)	۱ <sub>rr</sub>	]		20		А	1	
Application circuit operation: Set to VAC=20	00V, and V <sub>O</sub> =380	V						
Power factor	cosø	Wo=400W	0.9	0.95			Fig 44	
		Wo=2kW	0.98	0.99	1.0		Fig.11	

## Package Dimensions

unit:mm (typ)



### **Block Diagram**



#### **Pin Functions**

Pin No.	Pin Name	Description
1	Vs	Operating supply voltage (+18V Reg. input)
2	V <sub>CC</sub>	+18V V <sub>CC</sub> power supply output
3	GND	GND pin
4	ONF	ON/OFF control pin
5	VDET	Multiplication input
6	V <sub>REF</sub>	+5V reference voltage output
7	SS	Soft start pin
8	СТ	Operating frequency setting pin
9	IS	Current detection signal
10	IFB	Phase compensation (current amplification output)
11	IEI	Current amplification input
12	VEI	Output voltage control input
13	OVP	Overvoltage limiting
14	-	No connection
15	E	TR2, 3 (IGBT) emitter
16, 17	-	No connection
18	С	TR2, 3 (IGBT) collector
19	А	D2 (FRD) anode
20, 21	-	No connection
22	К	D2 (FRD) cathode

## **Test Circuit**

1: IR, ICES

	TR1	D2
А	18	22
В	15	19









3: V<sub>F</sub> (Test by pulse)

	D2	D3
А	19	15
В	22	18







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#### 5: ICC(ON)/ICC(OFF), VREF, fosc



#### 6: Vr, VTHOCP

А

в

Vr

12

9



#### 7: VTHOVP, ICHG



### STK760-221A-E



## **Sample Application Circuit**



\* When using the IC in a system having an input power voltage of 200V, insert a rush current limiting circuit, which consists of a limiting resistor Ri and a switch, to prevent the internal diodes from being damaged by the charging current from the output capacitor

#### **Recommended conditions**

Parameter Symbol		Conditions	Recommended values	unit
Commercial AC voltage	VAC	50/60Hz	170 to 264	Vrms
Output voltage	VO		VAC×√2+(10 to 15)≤ 450	V
Output overvoltage detection voltage	VOV		V <sub>OUT</sub> +(10 to 20)	V
Supply voltage (Pin 1)	Vs		21 to 40	V



#### **Timing Charts**

The IC will never be subjected to fatal damage when a power supply input or signals are applied or are not applied at any timing. If the  $V_{IN}$  (DC) input is applied to the IC at the timing shown in Figure 12 or 13, however, since the soft start circuit is inactive in this case, it is likely that the overcurrent protection circuit is activated and audible tone is generated out of the coil. To avoid this area of timing, it is necessary that the ON/OFF or V<sub>CC</sub> input be applied after V<sub>IN</sub> (DC).



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